

Disorder and Integral Quantum Hall Effect

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PACS number: 71.55 Jv, 72.20 My, 73.20 Jc

Abstract

The quantum Hall conductance of a disordered two-dimensional gas of non-interacting electrons is re-examined for its integrity against disorder in the limit of no mixing between different Landau levels. The exact one-electron eigenstates of the disordered system are shown to be current carrying, with exactly the same Hall current as in the absence of disorder. There are no localized states. Accordingly, each extensively degenerate Landau level, now broadened out by the disorder, continues to contribute exactly one quantum of Hall conductance ($e^2/2\pi\hbar$). In the absence of any localized (non-current carrying) states, the Hall plateaus can now arise only through an actual gap in the density of states separating the broadened Landau levels. Implications for 2D localization are discussed.

The Hall conductance σ_{xy} of a two-dimensional spin-polarized electron gas (2DEG) is well known to be stepped in units of the quantum of conductance $e^2/2\pi\hbar$. This is the Integral Quantum Hall Effect (IQHE).^{1,2} Such a 2D electron system obtains as an inversion/accumulation layer in a gated Si MOS-FET (metal-oxide semiconductor field effect transistor) or a modulation doped GaAs-AlGaAs heterostructure.³ The quantized conductance steps are observed experimentally as function of the strength of the external magnetic field (B) applied perpendicular to the plane of the 2DEG. The field tunes the density-of-states in the Landau levels, and thus controls their filling for a fixed areal

number density of electrons. Alternatively, one can vary the bias (the gate) voltage V_g that tunes the areal number density of electrons of the 2DEG and thus, for a fixed magnetic field, again controls the filling of the Landau levels. The conductance steps are separated by plateaus of constant conductance. While the conductance steps are of a universal height, the plateau-widths are sample dependent. There are gauge-theoretic global arguments for the universality of the quantized conductance steps.^{4,5} The observed accuracy of quantization of the Hall conductance, to better than 1 part in 10^7 , corroborates well with the robustness of these general arguments. In order to view the present work in the proper perspective, we have to review briefly the generally accepted explanation for the plateaus. The plateaus are supposed to arise as a consequence of the disorder induced Anderson localization in the imperfect samples.⁶ Disorder, which is ubiquitous, is expected to broaden out an otherwise extensively degenerate Landau level over an energy interval (Δ , say) centered at the unperturbed Landau level. Further, the tail states (away from the centre) are assumed to get localized and separated from the extended middle states by mobility edges. Now, as the *Fermi-level is swept* through these localized states, by varying the gate voltage, say, one expects no change in the Hall current – the filling/emptying of the non-current carrying (localized) states can not alter the total current. And hence the conductance plateaus. The width of the plateau then corresponds to the energy interval between the two mobility edges separating the adjacent Landau levels. The step, on the other hand, corresponds to the transit of the Fermi-level across the band of extended middle states between two mobility edges bracketing a given Landau level – gradual filling/emptying of these current carrying states changes the

total Hall current. The above widely accepted argument clearly implies that the plateau is not due to any gap in the density of states separating the Landau levels. It is rather due to the mobility gap – the localization of the tail states that lie between the impurity-broadened Landau levels. Indeed, in this picture no disorder would mean no plateaus, and hence no experimental visualization of the IQHE-steps.⁶ The quantization of the Hall conductance ($e^2/2\pi\hbar$ per Landau level) would, of course, demand then that the loss of the Hall current due to localization of some of the states be made up exactly by a correspondingly extra current to be carried by what extended states there might still be there.⁶ On the other extreme, strong disorder is also known to wipe out the IQHE. This picture has motivated detailed studies^{6,7} of the effect of some model impurity potentials, e.g., delta-function, on the Hall conductance and on the spatial distribution of the Hall current. It has also led to detailed numerical and theoretical discussion of the localization of eigenfunctions and of the spectral aspect of the IQHE in the presence of disorder.^{8–13} More specifically, it has been argued that in the limit of strong field (B), or weak disorder (Δ), there exists a single critical sub-extensively degenerate extended-state level at the centre of the impurity broadened Landau level, rather than a band of extended middle states separated from the localized tail states by mobility edges.^{8,9} In the limit of weak field, however, these extended states are believed to *float-up* energetically so as to conform to known absence of extended states in a 2D disordered system in zero field.^{10–13}

The present work addresses questions relating precisely to these fundamental aspects. In particular, we show that (1) the exact one-electron eigenstates of the disordered magnetized 2DEG in the QHE geometry are all current-

carrying, (2) these exact one-electron eigenstates carry exactly the same current as the corresponding unperturbed eigenstates do in the absence of disorder, and (3) the conductance plateaus arise then from the actual gap in the density of states separating the adjacent Landau levels. Our treatment of IQHE is exact in the absence of inter-Landau level mixing due to disorder. This would correspond to the adiabatic limit⁷ of high magnetic field giving the Landau-level spacing $\gg$ random impurity potential fluctuation on the magnetic length scale. Thus, except for the abrupt, or singular potentials, e.g., a delta-function, the neglect of inter-level mixing is believed to be valid in the high-field limit despite the corresponding enhancement of degeneracy.¹⁴ In any case there is no exact microscopic theory, to the best of our knowledge, that takes into account the inter-level mixing due to disorder. Also, we note that we are concerned here with IQHE and not the Fractional Quantum Hall Effect (FQHE),¹⁵ $\sigma_{xy} = \nu e^2/2\pi\hbar$ with $\nu = 1/3, 2/5, 2/3, \dots$. This is known to be essentially a many-body problem involving electron-electron interaction in a fractionally filled Landau level.¹⁶ Some of our exact results, however, do remain valid in the presence of interaction, again in the absence of any inter-level configurational mixing.

Let the sample $L_x \times L_y$ be magnetized with a uniform magnetic field $\mathbf{B} = -B\hat{z}$ along the z-axis, and electrified with an electric field along the x-axis giving a bias potential $V(x) = -|e|E_x x$. Let the total Hall current for this QHE-geometry be $\mathbf{J} = J\hat{y}$ along the y-axis. We will assume the thermodynamic limit ($L_x, L_y \rightarrow \infty$) and zero temperature throughout. The one-electron Hamiltonian H with the vector potential $\mathbf{A} = (0, -Bx)$ in the Landau gauge

is then

$$H = H_o + H_1 \quad (1)$$

with the unperturbed Hamiltonian (without disorder)

$$H_o = -\frac{1}{2m} \left(-i\hbar \frac{\partial}{\partial x} \right)^2 - \frac{1}{2m} \left(-i\hbar \frac{\partial}{\partial y} - |e| Bx \right)^2 - |e| E_x, \quad (2)$$

and H_1 the perturbation due to the potential disorder. The unperturbed Landau-Stark Hamiltonian has the well known eigenstates and eigenvalues.⁶

$$\begin{aligned} \psi_{pn}^o(x, y) &= A_n^{-1/2} \exp(ip_y/\hbar) \exp \left[-\frac{1}{2} \left(\frac{x - x_p}{l} \right)^2 \right] \dot{H}_n \left(\frac{x - x_p}{l} \right) \\ E_{np}^o &= \hbar w_c \left(n + \frac{1}{2} \right) + \left(\frac{cE}{B} \right) p, \end{aligned} \quad (3)$$

where $l = (\frac{\hbar c}{|e|B})^{1/2}$ the magnetic length, $w_c = |e| B/mc$ the cyclotron frequency, $p = \left(\frac{2\pi\hbar}{L_y} \right) k$ with $k = 0, \pm 1, \pm 2, \dots$ for periodic boundary condition in the y -direction, and $x_p = \frac{mc^2 E}{|e|B^2} - \frac{c}{|e|B} p$. Also, we have the normalization constant $A_n = (\pi^{1/2} l L_y 2^n n!)^{-1/2}$. These exact eigenstates are readily seen to be current carrying. The operator for the y -component of the total current (the Hall current) is

$$\hat{J}_y = -\frac{|e|}{L_y} \frac{1}{m} \left(-i\hbar \frac{\partial}{\partial y} - \frac{|e|}{c} Bx \right) \quad (4)$$

We readily verify that its expectation value in the eignstate $\psi_{np} \equiv |np\rangle$ is

$$J_y \equiv \langle np | \hat{J} | np \rangle = |e| c \frac{E}{BL_y} \equiv J_o. \quad (5)$$

Thus, each eignfunction carries exactly the same current J_o .

With these elementary results for the unperturbed system (H_o) in hand, we will now show that the exact eigenstates of the disordered system (H), unknown as they may be, are also current carrying, and that each of these

carries exactly the same Hall current as in the absence of disorder (H_1) so long as we assume no inter-Landau-Level mixing. For this, consider the effect of disorder H_1 on the Landau level n . Inasmuch as the exact eigenstates ψ_{np}^o of H_o form effectively a complete set of functions for the Landau level (n), because of no inter-level mixing, we can express the i^{th} exact eigenstate, ψ_n^i , as a linear combination of the unperturbed ψ_{np}^o 's :

$$| \psi_n^i \rangle = \sum_p C_{np}^i | \psi_{np} \rangle \quad (6)$$

with the unitarity condition on the coefficients C_{np}^i

$$\sum_n C_{np}^{i*} C_{np}^i = \delta_{pp'} \quad (7)$$

We now consider the expectation value of $\hat{J}_y$ in this new exact eigenstate

$$\begin{aligned} \langle \psi_n^i | \hat{J}_y | \psi_n^i \rangle &= \sum_{pp'} C_{np'}^{i*} C_{np}^i \langle \psi_{np'}^o | \hat{J} | \psi_{np}^i \rangle \\ &= \sum_{pp'} C_{np'}^{i*} C_{np}^i \delta_{pp'} \frac{|e| cE}{B} \\ &= \frac{|e| cE}{B} \equiv J_o \end{aligned} \quad (8)$$

In deriving Eq (8) we have made use of the fact that

$$\langle \psi_{np} | \frac{|e| Bx}{c} | \psi_{np} \rangle = \delta_{pp'} \left(-p + \frac{mcE}{B} \right) \quad (9)$$

Thus, the exact eigenstates of the disordered (electrified) Quantum Hall system, obtained by a general unitary mixing within the sub-space of a given Landau level, carry exactly the same total Hall current as in the absence of disorder. This is our main observation. Clearly, the total Hall current for the filled Landau level would then be $\frac{J_o L_x L_y}{2\pi l^2}$, giving Hall conductance per Landau level $\left(\frac{J_o L_x L_y}{2\pi l^2} \right) / L_x E = \left(\frac{|e|^2}{h} \right)$, just as for the pure system. This last result

remains valid in the presence of electron-electron interaction as well, so long as we assume no inter-Landau level configurational mixing: A completely fixed (impurity broadened) Landau level described by a determinantal wave function constructed from the exact ψ_n^i 's for a given level n , clearly contributes exactly the same Hall current and hence the same Hall conductance.

The above exact results have important consequences for the interpretation of IQHE, for the plateaus in particular, and for the question of Anderson localization in 2 dimensions in the presence of a strong perpendicular magnetic field in general. Given our result that the exact eigenstates of the disordered system are all current carrying and that there are no localized states, the conventional picture of capacitive (C) charging ($Q = CV_g$) of the 2D interface by the gate voltage (V_g) would produce a linear I-V characteristics *sans* plateaus — even in the presence of spectral gaps in the density of states. In our view the resolution of this paradox lies in the realization that the capacitance C above has been mistakenly taken to be the geometrical capacitance. The latter is valid when the electrodes are metallic and therefore with no gaps in the density of states. In the presence of the spectral gap between the (broadened) Landau levels, however, one must re-calculate the effective interfacial capacitance from the general expression for the charging energy that now must include the energy required to promote the electron across the gap in the density of states. This *quantum* capacitance would then become a non-trivial function of V_g itself. One expects the width of the plateau in terms V_g to reflecting the gapping of the spectrum. (For, a sufficiently disordered system, however, when the broadened Landau levels bridge the inter-level gaps, this would lead to no-plateaus, in agreement with the known result that IQHE disappears in very

dirty (strongly disordered) samples.⁶ Of course, in this limit, strictly speaking, our assumption of no inter-level mixing also becomes an approximation.) As for the localization in a disordered 2DEG in the presence of strong perpendicular magnetic field (and, of course, a weak cross-electric field, the gate voltage V_g that can be taken to be arbitrarily small), our result (Eq. 8) casts serious doubts on the picture of a (sub-extensively) degenerate, critical Landau level of extended current carrying states bracketed by localized insulating tail states controlling the IQHE in the strong field limit. One may have to consider the possibility of having weakly localizable (normalizable) eigenstates that nevertheless carry the Hall current. Alternative would be to suspect the condition of no inter-Landau mixing no matter how strong the magnetic field B is, due presumably to the corresponding enhancement of the degeneracy of the Landau level. Our strong-field results with no mixing, however, do not contradict the numerical results¹³ obtained in the weak field limit that suggest the *floating-up* of the central extended Landau states as $B \rightarrow 0$.

We would like to make a final observation in connection with the 2D localization in a perpendicular magnetic field. It is to be noted that in the absence of inter-level mixing the unperturbed ψ_{np}^o 's can be taken as a complete set of basis functions (for a given level n) labeled by the quasi-continuous index p , giving effectively a 1D tight-binding disordered Hamiltonian. An unusual feature of this Hamiltonian, however, is that the off-diagonal matrix elements are *essentially complex* random variables in that the Peierls-Landau phase factors can not be gauged away despite the one-dimensionality. This is because the off-diagonal matrix elements are not *nearest-neighbouring only* on the 1D quasi continuous p -lattice. The diagonal (real) matrix elements, of course, self-

average to zero, given the *extended* nature of $\psi_{np}^o(x, y)$. Such a 1D system with off-diagonal disorder calls for a detailed study, particularly in view of the well known result for the case of a nearest-neighbour tight-binding Hamiltonian with off-diagonal disorder, namely that the state at the centre of the band is always extended.

In conclusion, we have shown that the exact eigenstates of a disordered 2-dimensional electron gas in a perpendicular field are all current carrying. There are no localized states. Hall plateaus are due to spectral gaps and not the mobility gaps. These results are exact in the adiabatic limit of no inter-level mixing, valid for strong magnetic field, or equivalently for weak disorder.

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